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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-2vq100">https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-2vq100</a>

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## 2 – Low Power Modes in ProASIC3/E and ProASIC3 nano FPGAs

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### Introduction

The demand for low power systems and semiconductors, combined with the strong growth observed for value-based FPGAs, is driving growing demand for low power FPGAs. For portable and battery-operated applications, power consumption has always been the greatest challenge. The battery life of a system and on-board devices has a direct impact on the success of the product. As a result, FPGAs used in these applications should meet low power consumption requirements.

ProASIC<sup>®</sup>3/E and ProASIC3 nano FPGAs offer low power consumption capability inherited from their nonvolatile and live-at-power-up (LAPU) flash technology. This application note describes the power consumption and how to use different power saving modes to further reduce power consumption for power-conscious electronics design.

### Power Consumption Overview

In evaluating the power consumption of FPGA technologies, it is important to consider it from a system point of view. Generally, the overall power consumption should be based on static, dynamic, inrush, and configuration power. Few FPGAs implement ways to reduce static power consumption utilizing sleep modes.

SRAM-based FPGAs use volatile memory for their configuration, so the device must be reconfigured after each power-up cycle. Moreover, during this initialization state, the logic could be in an indeterminate state, which might cause inrush current and power spikes. More complex power supplies are required to eliminate potential system power-up failures, resulting in higher costs. For portable electronics requiring frequent power-up and -down cycles, this directly affects battery life, requiring more frequent recharging or replacement.

$$\text{SRAM-Based FPGA Total Power Consumption} = P_{\text{static}} + P_{\text{dynamic}} + P_{\text{inrush}} + P_{\text{config}}$$

EQ 1

$$\text{ProASIC3/E Total Power Consumption} = P_{\text{static}} + P_{\text{dynamic}}$$

EQ 2

Unlike SRAM-based FPGAs, Microsemi flash-based FPGAs are nonvolatile and do not require power-up configuration. Additionally, Microsemi nonvolatile flash FPGAs are live at power-up and do not require additional support components. Total power consumption is reduced as the inrush current and configuration power components are eliminated.

Note that the static power component can be reduced in flash FPGAs (such as the ProASIC3/E devices) by entering User Low Static mode or Sleep mode. This leads to an extremely low static power component contribution to the total system power consumption.

The following sections describe the usage of Static (Idle) mode to reduce the power component, User Low Static mode to reduce the static power component, and Sleep mode and Shutdown mode to achieve a range of power consumption when the FPGA or system is idle. Table 2-1 on page 22 summarizes the different low power modes offered by ProASIC3/E devices.

Table 2-4 shows the current draw in Sleep mode for an A3P250 device with the following test conditions: VCCI = VMV; VCC = VJTAG = VPUMP = GND.

**Table 2-4 • A3P250 Current Draw in Sleep Mode**

Typical Conditions	A3P250	
	I <sub>CCI</sub> (μA)	I <sub>CCI</sub> (μA) per Bank
VCCI = 3.3 V	31.57	7.89
VCCI = 2.5 V	23.96	5.99
VCCI = 1.8 V	17.32	4.33
VCCI = 1.5 V	14.46	3.62
I <sub>CC</sub> FPGA Core	0.0	0.0
Leakage Current per I/O	0.1	0.1
VPUMP	0.0	0.0

*Note: The data in this table were taken under typical conditions and are based on characterization. The data is not guaranteed.*

Table 2-5 shows the current draw in Sleep mode for an A3PE600 device with the following test conditions: VCCI = VMV; VCC = VJTAG = VPUMP = GND.

**Table 2-5 • A3PE600 Current Draw in Sleep Mode**

Typical Conditions	A3PE600	
	I <sub>CCI</sub> (μA)	I <sub>CCI</sub> (μA) per Bank
VCCI = 3.3 V	59.85	7.48
VCCI = 2.5 V	45.50	5.69
VCCI = 1.8 V	32.98	4.12
VCCI = 1.5 V	27.66	3.46
VCCI = 0 V or Floating	0.0	0.0
I <sub>CC</sub> FPGA Core	0.0	0.0
Leakage Current per I/O	0.1	0.1
I <sub>PUMP</sub>	0.0	0.0

*Note: The data in this table were taken under typical conditions and are based on characterization. The data is not guaranteed.*

ProASIC3/E and ProASIC3 nano devices were designed such that before device power-up, all I/Os are in tristate mode. The I/Os will remain tristated during power-up until the last voltage supply (VCC or VCCI) is powered to its functional level. After the last supply reaches the functional level, the outputs will exit the tristate mode and drive the logic at the input of the output buffer. The behavior of user I/Os is independent of the VCC and VCCI sequence or the state of other FPGA voltage supplies (VPUMP and VJTAG). During power-down, device I/Os become tristated once the first power supply (VCC or VCCI) drops below its brownout voltage level. The I/O behavior during power-down is also independent of voltage supply sequencing.

Figure 2-5 on page 27 shows a timing diagram for the FPGA core entering the activation and deactivation trip points for a typical application when the VCC power supply ramp rate is 100 μs (ramping from 0 V to 1.5 V). This is, in fact, the timing diagram for the FPGA entering and exiting Sleep mode, as it is dependent on powering down or powering up VCC. Depending on the ramp rate of the power supply and board-level configurations, the user can easily calculate how long it takes for the core to become active or inactive. For more information, refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 307.



## Spine Architecture

The low power flash device architecture allows the VersaNet global networks to be segmented. Each of these networks contains spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside its region. The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that the number of quadrant globals and globals/spines per tree varies depending on the specific device. Refer to Table 3-4 for the clocking resources available for each device. The spines are the vertical branches of the global network tree, shown in Figure 3-3 on page 34. Each spine in a vertical column of a chip (main) global network is further divided into two spine segments of equal lengths: one in the top and one in the bottom half of the die (except in 10 k through 30 k gate devices).

Top and bottom spine segments radiating from the center of a device have the same height. However, just as in the ProASIC<sup>PLUS</sup> family, signals assigned only to the top and bottom spine cannot access the middle two rows of the die. The spines for quadrant clock networks do not cross the middle of the die and cannot access the middle two rows of the architecture.

Each spine and its associated ribs cover a certain area of the device (the "scope" of the spine; see Figure 3-3 on page 34). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or by another net defined by the user. Details of the chip (main) global network spine-selection MUX are presented in Figure 3-8 on page 44. The spine drivers for each spine are located in the middle of the die.

Quadrant spines can be driven from user I/Os or an internal signal from the north and south sides of the die. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design. Access to the top quadrant spine regions is from the top of the die, and access to the bottom quadrant spine regions is from the bottom of the die. The A3PE3000 device has 28 clock trees and each tree has nine spines; this flexible global network architecture enables users to map up to 252 different internal/external clocks in an A3PE3000 device.

**Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices**

ProASIC3/ ProASIC3L Devices	IGLOO Devices	Chip Globals	Quadrant Globals (4x3)	Clock Trees	Globals/ Spines per Tree	Total Spines per Device	VersaTiles in Each Tree	Total VersaTiles	Rows in Each Spine
A3PN010	AGLN010	4	0	1	0	0	260	260	4
A3PN015	AGLN015	4	0	1	0	0	384	384	6
A3PN020	AGLN020	4	0	1	0	0	520	520	6
A3PN060	AGLN060	6	12	4	9	36	384	1,536	12
A3PN125	AGLN125	6	12	8	9	72	384	3,072	12
A3PN250	AGLN250	6	12	8	9	72	768	6,144	24
A3P015	AGL015	6	0	1	9	9	384	384	12
A3P030	AGL030	6	0	2	9	18	384	768	12
A3P060	AGL060	6	12	4	9	36	384	1,536	12
A3P125	AGL125	6	12	8	9	72	384	3,072	12
A3P250/L	AGL250	6	12	8	9	72	768	6,144	24
A3P400	AGL400	6	12	12	9	108	768	9,216	24
A3P600/L	AGL600	6	12	12	9	108	1,152	13,824	36
A3P1000/L	AGL1000	6	12	16	9	144	1,536	24,576	48
A3PE600/L	AGLE600	6	12	12	9	108	1,120	13,440	35
A3PE1500		6	12	20	9	180	1,888	37,760	59
A3PE3000/L	AGLE3000	6	12	28	9	252	2,656	74,368	83

## Simple Design Example

Consider a design consisting of six building blocks (shift registers) and targeted for an A3PE600-PQ208 (Figure 3-16 on page 52). The example design consists of two PLLs (PLL1 has GLA only; PLL2 has both GLA and GLB), a global reset (ACLR), an enable (EN\_ALL), and three external clock domains (QCLK1, QCLK2, and QCLK3) driving the different blocks of the design. Note that the PQ208 package only has two PLLs (which access the chip global network). Because of fanout, the global reset and enable signals need to be assigned to the chip global resources. There is only one free chip global for the remaining global (QCLK1, QCLK2, QCLK3). Place two of these signals on the quadrant global resource. The design example demonstrates manually assignment of QCLK1 and QCLK2 to the quadrant global using the PDC command.

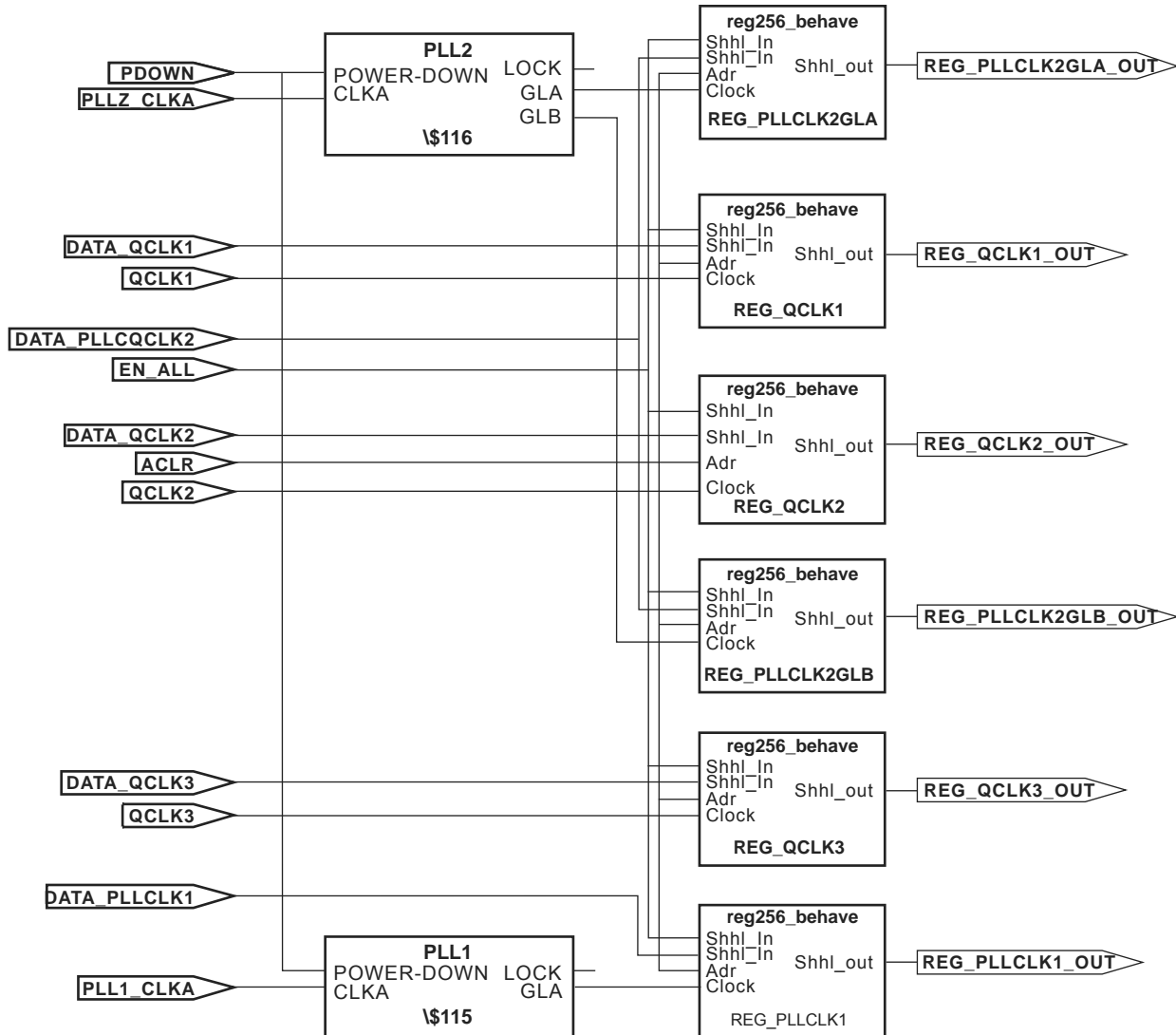


Figure 3-19 • Block Diagram of the Global Management Example Design

## Global Buffers with No Programmable Delays

Access to the global / quadrant global networks can be configured directly from the global I/O buffer, bypassing the CCC functional block (as indicated by the dotted lines in Figure 4-1 on page 61). Internal signals driven by the FPGA core can use the global / quadrant global networks by connecting via the routed clock input of the multiplexer tree.

There are many specific CLKBUF macros supporting the wide variety of single-ended I/O inputs (CLKBUF) and differential I/O standards (CLKBUF\_LVDS/LVPECL) in the low power flash families. They are used when connecting global I/Os directly to the global/quadrant networks.

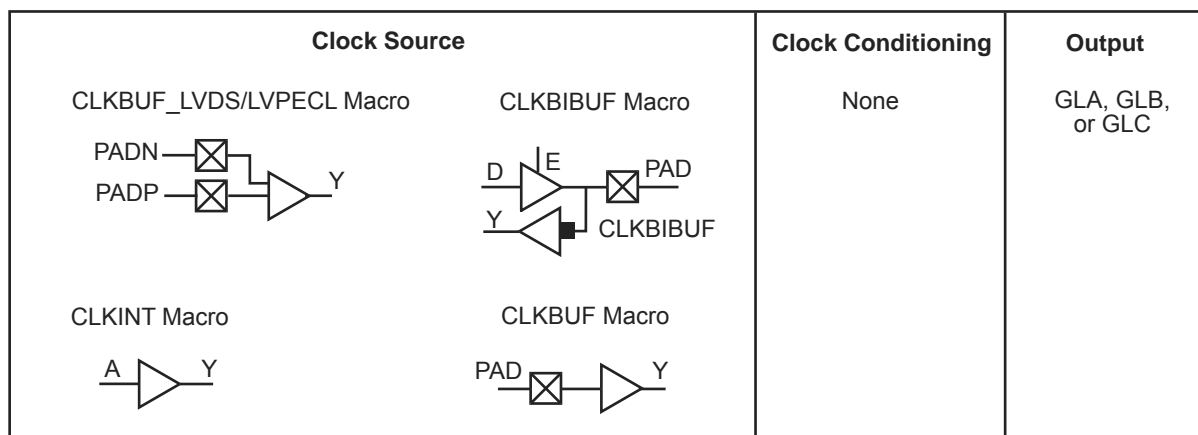
Note: IGLOO nano and ProASIC nano devices do not support differential inputs.

When an internal signal needs to be connected to the global/quadrant network, the CLKINT macro is used to connect the signal to the routed clock input of the network's MUX tree.

To utilize direct connection from global I/Os or from internal signals to the global/quadrant networks, CLKBUF, CLKBUF\_LVPECL/LVDS, and CLKINT macros are used (Figure 4-2).

- The CLKBUF and CLKBUF\_LVPECL/LVDS<sup>1</sup> macros are composite macros that include an I/O macro driving a global buffer, which uses a hardwired connection.
- The CLKBUF, CLKBUF\_LVPECL/LVDS<sup>1</sup> and CLKINT macros are pass-through clock sources and do not use the PLL or provide any programmable delay functionality.
- The CLKINT macro provides a global buffer function driven internally by the FPGA core.

The available CLKBUF macros are described in the *IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide*.



Note: IGLOO nano and ProASIC nano devices do not support differential inputs.

**Figure 4-2 • CCC Options: Global Buffers with No Programmable Delay**

## Global Buffer with Programmable Delay

Clocks requiring clock adjustments can utilize the programmable delay cores before connecting to the global / quadrant global networks. A maximum of 18 CCC global buffers can be instantiated in a device—three per CCC and up to six CCCs per device.

Each CCC functional block contains a programmable delay element for each of the global networks (up to three), and users can utilize these features by using the corresponding macro (Figure 4-3 on page 65).

1. B-LVDS and M-LVDS are supported with the LVDS macro.

This section outlines the following device information: CCC features, PLL core specifications, functional descriptions, software configuration information, detailed usage information, recommended board-level considerations, and other considerations concerning global networks in low power flash devices.

## **Clock Conditioning Circuits with Integrated PLLs**

Each of the CCCs with integrated PLLs includes the following:

- 1 PLL core, which consists of a phase detector, a low-pass filter, and a four-phase voltage-controlled oscillator
- 3 global multiplexer blocks that steer signals from the global pads and the PLL core onto the global networks
- 6 programmable delays and 1 fixed delay for time advance/delay adjustments
- 5 programmable frequency divider blocks to provide frequency synthesis (automatically configured by the SmartGen macro builder tool)

## **Clock Conditioning Circuits without Integrated PLLs**

There are two types of simplified CCCs without integrated PLLs in low power flash devices.

1. The simplified CCC with programmable delays, which is composed of the following:
  - 3 global multiplexer blocks that steer signals from the global pads and the programmable delay elements onto the global networks
  - 3 programmable delay elements to provide time delay adjustments
2. The simplified CCC (referred to as CCC-GL) without programmable delay elements, which is composed of the following:
  - A global multiplexer block that steer signals from the global pads onto the global networks

## Phase Adjustment

The four phases available (0, 90, 180, 270) are phases with respect to VCO (PLL output). The VCO is divided to achieve the user's CCC required output frequency (GLA, YB/GLB, YC/GLC). The division happens after the selection of the VCO phase. The effective phase shift is actually the VCO phase shift divided by the output divider. This is why the visual CCC shows both the actual achievable phase and more importantly the actual delay that is equivalent to the phase shift that can be achieved.

## Dynamic PLL Configuration

The CCCs can be configured both statically and dynamically.

In addition to the ports available in the Static CCC, the Dynamic CCC has the dynamic shift register signals that enable dynamic reconfiguration of the CCC. With the Dynamic CCC, the ports CLKB and CLKC are also exposed. All three clocks (CLKA, CLKB, and CLKC) can be configured independently.

The CCC block is fully configurable. The following two sources can act as the CCC configuration bits.

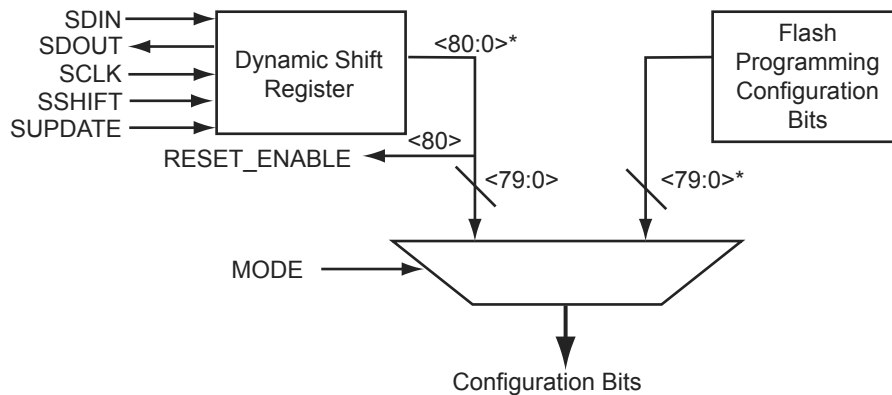
### Flash Configuration Bits

The flash configuration bits are the configuration bits associated with programmed flash switches. These bits are used when the CCC is in static configuration mode. Once the device is programmed, these bits cannot be modified. They provide the default operating state of the CCC.

### Dynamic Shift Register Outputs

This source does not require core reprogramming and allows core-driven dynamic CCC reconfiguration. When the dynamic register drives the configuration bits, the user-defined core circuit takes full control over SDIN, SDOUT, SCLK, SSHIFT, and SUPDATE. The configuration bits can consequently be dynamically changed through shift and update operations in the serial register interface. Access to the logic core is accomplished via the dynamic bits in the specific tiles assigned to the PLLs.

Figure 4-21 illustrates a simplified block diagram of the MUX architecture in the CCCs.



Note: \*For Fusion, bit <88:81> is also needed.

**Figure 4-21 • The CCC Configuration MUX Architecture**

The selection between the flash configuration bits and the bits from the configuration register is made using the MODE signal shown in Figure 4-21. If the MODE signal is logic HIGH, the dynamic shift register configuration bits are selected. There are 81 control bits to configure the different functions of the CCC.

Each group of control bits is assigned a specific location in the configuration shift register. For a list of the 81 configuration bits (C[80:0]) in the CCC and a description of each, refer to "PLL Configuration Bits Description" on page 90. The configuration register can be serially loaded with the new configuration data and programmed into the CCC using the following ports:

- **SDIN:** The configuration bits are serially loaded into a shift register through this port. The LSB of the configuration data bits should be loaded first.
- **SDOUT:** The shift register contents can be shifted out (LSB first) through this port using the shift operation.
- **SCLK:** This port should be driven by the shift clock.
- **SSHIFT:** The active-high shift enable signal should drive this port. The configuration data will be shifted into the shift register if this signal is HIGH. Once SSHIFT goes LOW, the data shifting will be halted.
- **SUPDATE:** The SUPDATE signal is used to configure the CCC with the new configuration bits when shifting is complete.

To access the configuration ports of the shift register (SDIN, SDOUT, SSHIFT, etc.), the user should instantiate the CCC macro in his design with appropriate ports. Microsemi recommends that users choose SmartGen to generate the CCC macros with the required ports for dynamic reconfiguration.

Users must familiarize themselves with the architecture of the CCC core and its input, output, and configuration ports to implement the desired delay and output frequency in the CCC structure.

Figure 4-22 shows a model of the CCC with configurable blocks and switches.

## 5 – FlashROM in Microsemi’s Low Power Flash Devices

### Introduction

The Fusion, IGLOO, and ProASIC3 families of low power flash-based devices have a dedicated nonvolatile FlashROM memory of 1,024 bits, which provides a unique feature in the FPGA market. The FlashROM can be read, modified, and written using the JTAG (or UJTAG) interface. It can be read but not modified from the FPGA core. Only low power flash devices contain on-chip user nonvolatile memory (NVM).

### Architecture of User Nonvolatile FlashROM

Low power flash devices have 1 kbit of user-accessible nonvolatile flash memory on-chip that can be read from the FPGA core fabric. The FlashROM is arranged in eight banks of 128 bits (16 bytes) during programming. The 128 bits in each bank are addressable as 16 bytes during the read-back of the FlashROM from the FPGA core. Figure 5-1 shows the FlashROM logical structure.

The FlashROM can only be programmed via the IEEE 1532 JTAG port. It cannot be programmed directly from the FPGA core. When programming, each of the eight 128-bit banks can be selectively reprogrammed. The FlashROM can only be reprogrammed on a bank boundary. Programming involves an automatic, on-chip bank erase prior to reprogramming the bank. The FlashROM supports synchronous read. The address is latched on the rising edge of the clock, and the new output data is stable after the falling edge of the same clock cycle. For more information, refer to the timing diagrams in the DC and Switching Characteristics chapter of the appropriate datasheet. The FlashROM can be read on byte boundaries. The upper three bits of the FlashROM address from the FPGA core define the bank being accessed. The lower four bits of the FlashROM address from the FPGA core define which of the 16 bytes in the bank is being accessed.

		Byte Number in Bank								4 LSB of ADDR (READ)							
		15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Bank Number 3 MSB of ADDR (READ)	7																
	6																
	5																
	4																
	3																
	2																
	1																
	0																

Figure 5-1 • FlashROM Architecture

SmartGen allows you to generate the FlashROM netlist in VHDL, Verilog, or EDIF format. After the FlashROM netlist is generated, the core can be instantiated in the main design like other SmartGen cores. Note that the macro library name for FlashROM is UFROM. The following is a sample FlashROM VHDL netlist that can be instantiated in the main design:

```
library ieee;
use ieee.std_logic_1164.all;
library fusion;

entity FROM_a is
    port( ADDR : in std_logic_vector(6 downto 0); DOUT : out std_logic_vector(7 downto 0));
end FROM_a;

architecture DEF_ARCH of FROM_a is

    component UFROM
        generic (MEMORYFILE:string);
        port(DO0, DO1, DO2, DO3, DO4, DO5, DO6, DO7 : out std_logic;
            ADDR0, ADDR1, ADDR2, ADDR3, ADDR4, ADDR5, ADDR6 : in std_logic := 'U') ;
    end component;

    component GND
        port( Y : out std_logic);
    end component;

    signal U_7_PIN2 : std_logic ;

begin

    GND_1_net : GND port map(Y => U_7_PIN2);
    UFROM0 : UFROM
        generic map(MEMORYFILE => "FROM_a.mem")
        port map(DO0 => DOUT(0), DO1 => DOUT(1), DO2 => DOUT(2), DO3 => DOUT(3), DO4 => DOUT(4),
            DO5 => DOUT(5), DO6 => DOUT(6), DO7 => DOUT(7), ADDR0 => ADDR(0), ADDR1 => ADDR(1),
            ADDR2 => ADDR(2), ADDR3 => ADDR(3), ADDR4 => ADDR(4), ADDR5 => ADDR(5),
            ADDR6 => ADDR(6));

end DEF_ARCH;
```

SmartGen generates the following files along with the netlist. These are located in the SmartGen folder for the Libero SoC project.

1. MEM (Memory Initialization) file
2. UFC (User Flash Configuration) file
3. Log file

The MEM file is used for simulation, as explained in the "Simulation of FlashROM Design" section on page 127. The UFC file, generated by SmartGen, has the FlashROM configuration for single or multiple devices and is used during STAPL generation. It contains the region properties and simulation values. Note that any changes in the MEM file will not be reflected in the UFC file. Do not modify the UFC to change FlashROM content. Instead, use the SmartGen GUI to modify the FlashROM content. See the "Programming File Generation for FlashROM Design" section on page 127 for a description of how the UFC file is used during the programming file generation. The log file has information regarding the file type and file location.



## Software Support

The SmartGen core generator is the easiest way to select and configure the memory blocks (Figure 6-12). SmartGen automatically selects the proper memory block type and aspect ratio, and cascades the memory blocks based on the user's selection. SmartGen also configures any additional signals that may require tie-off.

SmartGen will attempt to use the minimum number of blocks required to implement the desired memory. When cascading, SmartGen will configure the memory for width before configuring for depth. For example, if the user requests a 256×8 FIFO, SmartGen will use a 512×9 FIFO configuration, not 256×18.

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**Figure 6-12 • SmartGen Core Generator Interface**

## I/O Architecture

### I/O Tile

IGLOO and ProASIC3 nano devices utilize either a single-tile or dual-tile I/O architecture (Figure 7-1 on page 159 and Figure 7-2 on page 160). The 10 k, 15 k, and 20 k devices utilize the single-tile design and the 60 k, 125 k and 250 k devices utilize the dual-tile design. In both cases, the I/O tile provides a flexible, programmable structure for implementing a large number of I/O standards. In addition, the registers available in the I/O tile can be used to support high-performance register inputs and outputs, with register enable if desired. For single-tile designs, all I/O registers share both the CLR and CLK ports, while for the dual-tile designs, the output register and output enable register share one CLK port. For the dual-tile designs, the registers can also be used to support the JESD-79C Double Data Rate (DDR) standard within the I/O structure (see the "DDR for Microsemi's Low Power Flash Devices" section on page 205 for more information).

### I/O Registers

Each I/O module contains several input and output registers. Refer to Figure 7-3 on page 165 for a simplified representation of the I/O block. The number of input registers is selected by a set of switches (not shown in Figure 7-2 on page 160) between registers to implement single-ended data transmission to and from the FPGA core. The Designer software sets these switches for the user. For single-tile designs, a common CLR/PRE signal is employed by all I/O registers when I/O register combining is used. The I/O register combining requires that no combinatorial logic be present between the register and the I/O.

## Software-Controlled I/O Attributes

Users may modify these programmable I/O attributes using the I/O Attribute Editor. Modifying an I/O attribute may result in a change of state in Designer. Table 8-2 details which steps have to be re-run as a function of modified I/O attribute.

**Table 8-2 • Designer State (resulting from I/O attribute modification)**

I/O Attribute	Designer States <sup>1</sup>				
	Compile	Layout	Fuse	Timing	Power
Slew Control <sup>2</sup>	No	No	Yes	Yes	Yes
Output Drive (mA)	No	No	Yes	Yes	Yes
Skew Control	No	No	Yes	Yes	Yes
Resistor Pull	No	No	Yes	Yes	Yes
Input Delay	No	No	Yes	Yes	Yes
Schmitt Trigger	No	No	Yes	Yes	Yes
OUT_LOAD	No	No	No	Yes	Yes
COMBINE_REGISTER	Yes	Yes	N/A	N/A	N/A

Notes:

1. No = Remains the same, Yes = Re-run the step, N/A = Not applicable
2. Skew control does not apply to IGLOO nano, IGLOO PLUS, and ProASIC3 nano devices.
3. Programmable input delay is applicable only for ProASIC3E, ProASIC3EL, RT ProASIC3, and IGLOOe devices.

## Instantiating DDR Registers

Using SmartGen is the simplest way to generate the appropriate RTL files for use in the design. Figure 9-4 shows an example of using SmartGen to generate a DDR SSTL2 Class I input register. SmartGen provides the capability to generate all of the DDR I/O cells as described. The user, through the graphical user interface, can select from among the many supported I/O standards. The output formats supported are Verilog, VHDL, and EDIF.

Figure 9-5 on page 211 through Figure 9-8 on page 214 show the I/O cell configured for DDR using SSTL2 Class I technology. For each I/O standard, the I/O pad is buffered by a special primitive that indicates the I/O standard type.

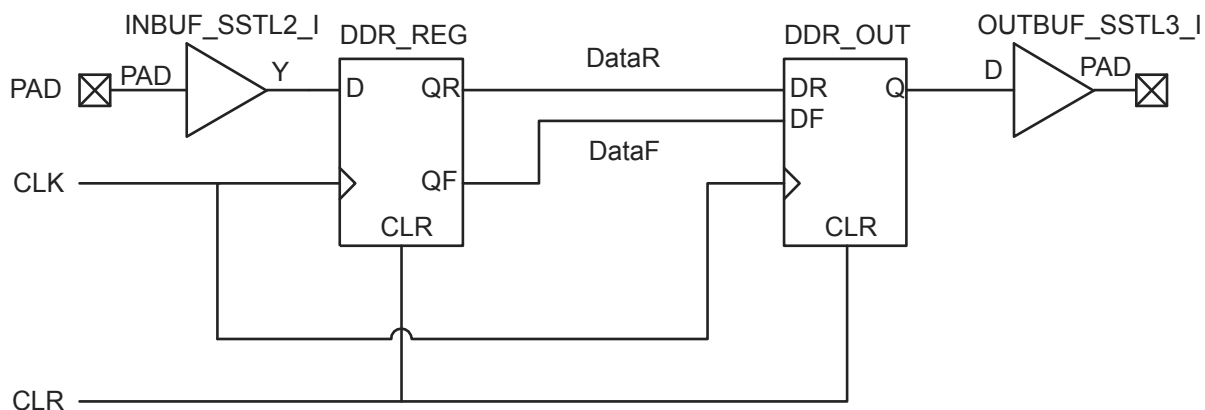
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**Figure 9-4 • Example of Using SmartGen to Generate a DDR SSTL2 Class I Input Register**

## Design Example

Figure 9-9 shows a simple example of a design using both DDR input and DDR output registers. The user can copy the HDL code in Libero SoC software and go through the design flow. Figure 9-10 and Figure 9-11 on page 217 show the netlist and ChipPlanner views of the ddr\_test design. Diagrams may vary slightly for different families.



**Figure 9-9 • Design Example**

**Figure 9-10 • DDR Test Design as Seen by NetlistViewer for IGLOO/e Devices**

**Table 11-5 • FlashLock Security Options for Fusion**

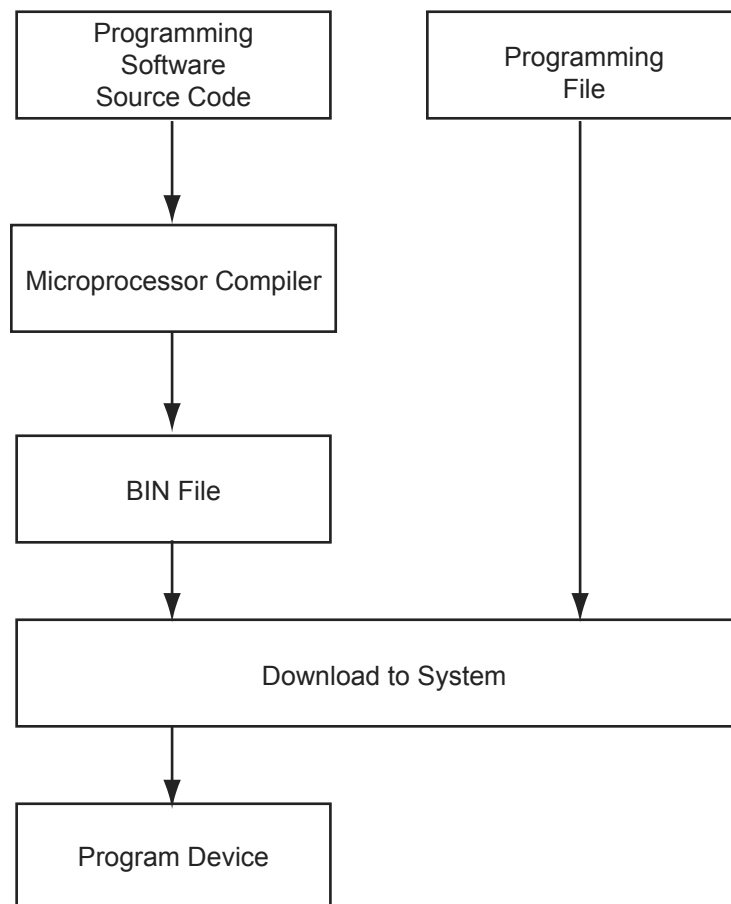
Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / no FlashLock	–	–	–	–
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

For this scenario, generate the programming file as follows:

1. Select only the **Security settings** option, as indicated in Figure 11-14 and Figure 11-15 on page 252. Click **Next**.

---

**Figure 11-14 • Programming IGLOO and ProASIC3 Security Settings Only**



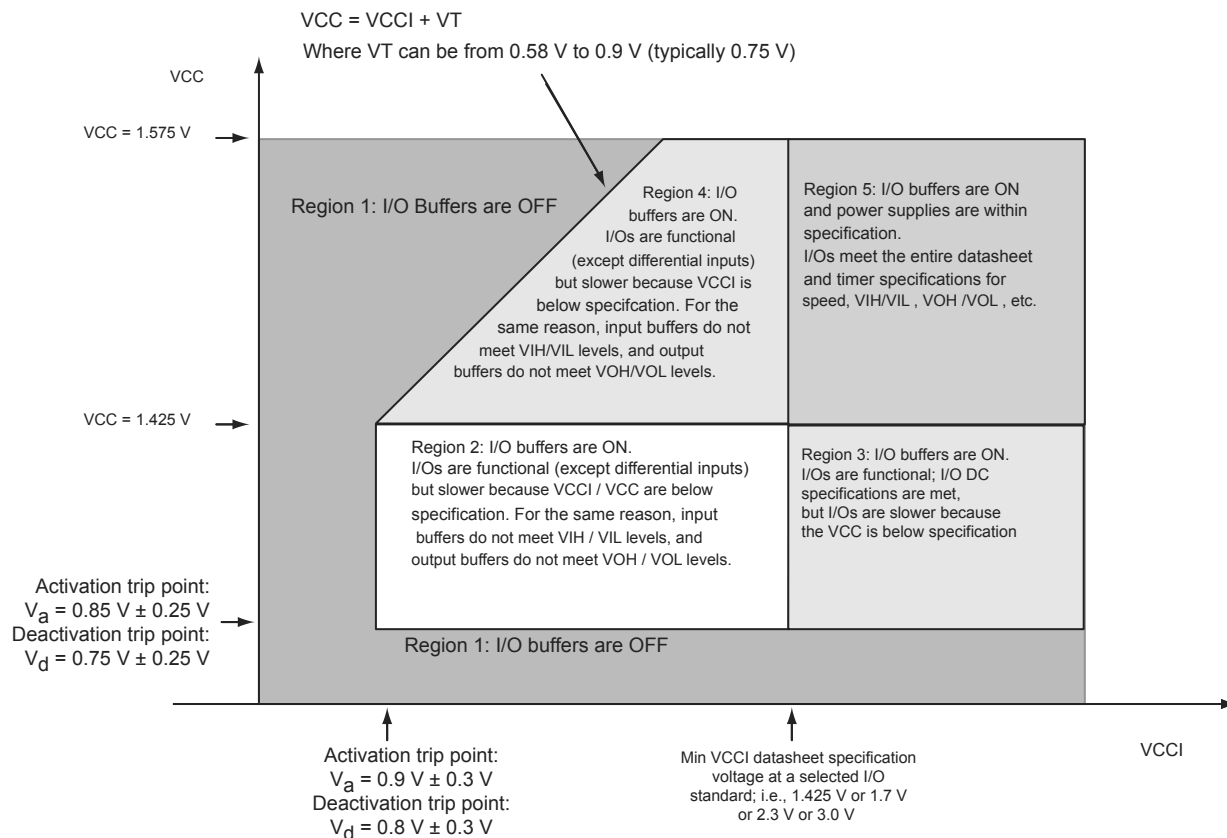
---

**Figure 14-3 • MCU FPGA Programming Model**

## FlashROM

Microsemi low power flash devices have 1 kbit of user-accessible, nonvolatile, FlashROM on-chip. This nonvolatile FlashROM can be programmed along with the core or on its own using the standard IEEE 1532 JTAG programming interface.

The FlashROM is architected as eight pages of 128 bits. Each page can be individually programmed (erased and written). Additionally, on-chip AES security decryption can be used selectively to load data securely into the FlashROM (e.g., over public or private networks, such as the Internet). Refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 117.



**Figure 17-4 • I/O State as a Function of  $VCCI$  and  $VCC$  Voltage Levels for IGLOO V5, IGLOO nano V5, IGLOO PLUS V5, ProASIC3L, and ProASIC3 Devices Running at  $VCC = 1.5 \text{ V} \pm 0.075 \text{ V}$**



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